

GigaDevice Semiconductor Inc.

**基于 GD32F3x0 系列的 IEC60730 ClassB 库
移植指南**

应用笔记

AN171

1.0 版本

(2023 年 10 月)

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1. 简介

GD32 MCU提供IEC60730 ClassB认证库支持，对于每个系列的GD32 MCU，都会提供常用系列的工程模板，用户在对同一系列不同型号的芯片进行IEC60730自检认证时，可通过移植模板程序来适配目标芯片。本应用笔记将详细介绍 GD32F3x0 系列芯片在不同 IDE（Keil/IAR/eclipse）下，移植过程中的注意事项，帮助客户移植IEC60730 ClassB认证库。

2. IEC60730 ClassB 认证库移植

GD32 MCU提供IAR、Keil、eclipse环境下的IEC60730 ClassB认证库支持，三种开发环境下模板工程的移植存在差异。下面将从三种开发环境展开说明。

本应用笔记基于GD32F350RB进行工程移植说明。

2.1. IAR 环境认证库工程移植

1、根据芯片数据手册修改gd32f3x0_test.h文件中编译宏__IAR_SYSTEMS_ICC__下的RAM边界，如[图2-1. 修改gd32f3x0_test.h中RAM边界](#)所示。

图 2-1. 修改 gd32f3x0_test.h 中 RAM 边界

```

#ifndef __IAR_SYSTEMS_ICC__
extern uint32_t __ICFEDIT_region_ROM_start__;
extern uint32_t __ICFEDIT_region_ROM_end__;
extern uint32_t __ICFEDIT_region_RAM_start__;
extern uint32_t __ICFEDIT_region_RAM_end__;
extern uint32_t __ICFEDIT_region_IECTEST_PARAM_start__;
extern uint32_t __ICFEDIT_region_IECTEST_PARAM_end__;

#define FLASH_START      ((unsigned int *)&__ICFEDIT_region_ROM_start__)
#define FLASH_SIZE      ((unsigned int)&__ICFEDIT_region_ROM_end__ - (unsigned int)&__ICFEDIT_region_ROM_start__ + 1) /* FLASH_SIZE in byte */
#define FLASH_SIZE_WORDS ((uint32_t)&__ICFEDIT_region_ROM_end__ - (uint32_t)&__ICFEDIT_region_ROM_start__ + 1)/4 /* FLASH_SIZE in words */
#define FLASH_END      ((uint32_t *)&__ICFEDIT_region_ROM_end__)

#define FLASH_BLOCK_SIZE ((uint32_t)512uL)
#define FLASH_BLOCKNUM  ((uint32_t)((FLASH_SIZE) / FLASH_BLOCK_SIZE))
#define FLASH_BLOCKNUM_WORDS ((uint32_t)(FLASH_SIZE_WORDS / FLASH_BLOCK_SIZE))

#define RAM_START      ((uint32_t *)0x20000000)
#define RAM_END      ((uint32_t *)0x20003f40)

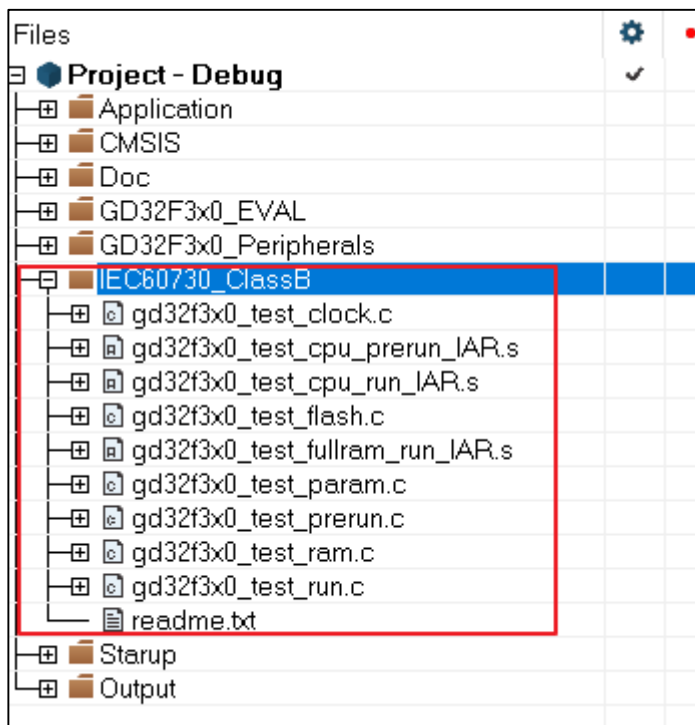
#define IEC_TEST_PARAM_START ((uint32_t *)(&__ICFEDIT_region_IECTEST_PARAM_start__))
#define IEC_TEST_PARAM_END ((uint32_t *)(&__ICFEDIT_region_IECTEST_PARAM_end__))

extern void __iar_program_start(void);
extern void Reset_Handler(void);
#define DefaultSystemStartup() Reset_Handler()

void test_fail_reset(void);

#endif /* __IAR_SYSTEMS_ICC__ */
    
```

图 2-2. 添加 ClassB 库文件到 IAR 工程



若启动文件符合当前芯片型号，则无需修改；若不符合，则需要在固件库文件夹 GD32F3x0_Firmware_Library\CMSIS\GD\GD32F3x0\Source\ARM 下，重新选择符合当前芯片类型的.s启动文件，并如[图2-3. 修改.s启动文件](#)所示进行修改，使芯片上电之后先进行自检。

图 2-3. 修改.s 启动文件

```

MODULE ?cstartup

;; Forward declaration of sections.
SECTION CSTACK:DATA:NOROOT(3)

SECTION .intvec:CODE:NOROOT(3)

EXTERN test_prerun

EXTERN __iar_program_start
EXTERN SystemInit
PUBLIC __vector_table

DATA
__vector_table
DCD sfe(CSTACK) ; top of stack
DCD test_prerun ; Vector Number 1, test_prerun

DCD NMI_Handler ; Vector Number 2, NMI Handler
DCD HardFault_Handler ; Vector Number 3, Hard Fault Handler
DCD MemManage_Handler ; Vector Number 4, MPU Fault Handler
DCD BusFault_Handler ; Vector Number 5, Bus Fault Handler
DCD UsageFault_Handler ; Vector Number 6, Usage Fault Handler
DCD 0 ; Reserved
DCD 0 ; Reserved
DCD 0 ; Reserved
DCD 0 ; Reserved
DCD SVC_Handler ; Vector Number 11, SVC Call Handler
DCD DebugMon_Handler ; Vector Number 12, Debug Monitor Handler
DCD 0 ; Reserved
DCD PendSV_Handler ; Vector Number 14, PendSV Handler
DCD SysTick_Handler ; Vector Number 15, SysTick Handler

```

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2、修改工程所在文件夹（在本例中为：..\GD32F3x0_IEC_Test\GD32350R_EVAL_Demo_Suites\Projects\IEC_Test\EWARM）下的IEC_TEST_BOOT_FLASH.icf文件，如[图2-4. 修改分散加载文件](#)所示为修改的部分，根据芯片数据手册修改Flash和RAM的大小适配当前芯片。

图 2-4. 修改分散加载文件

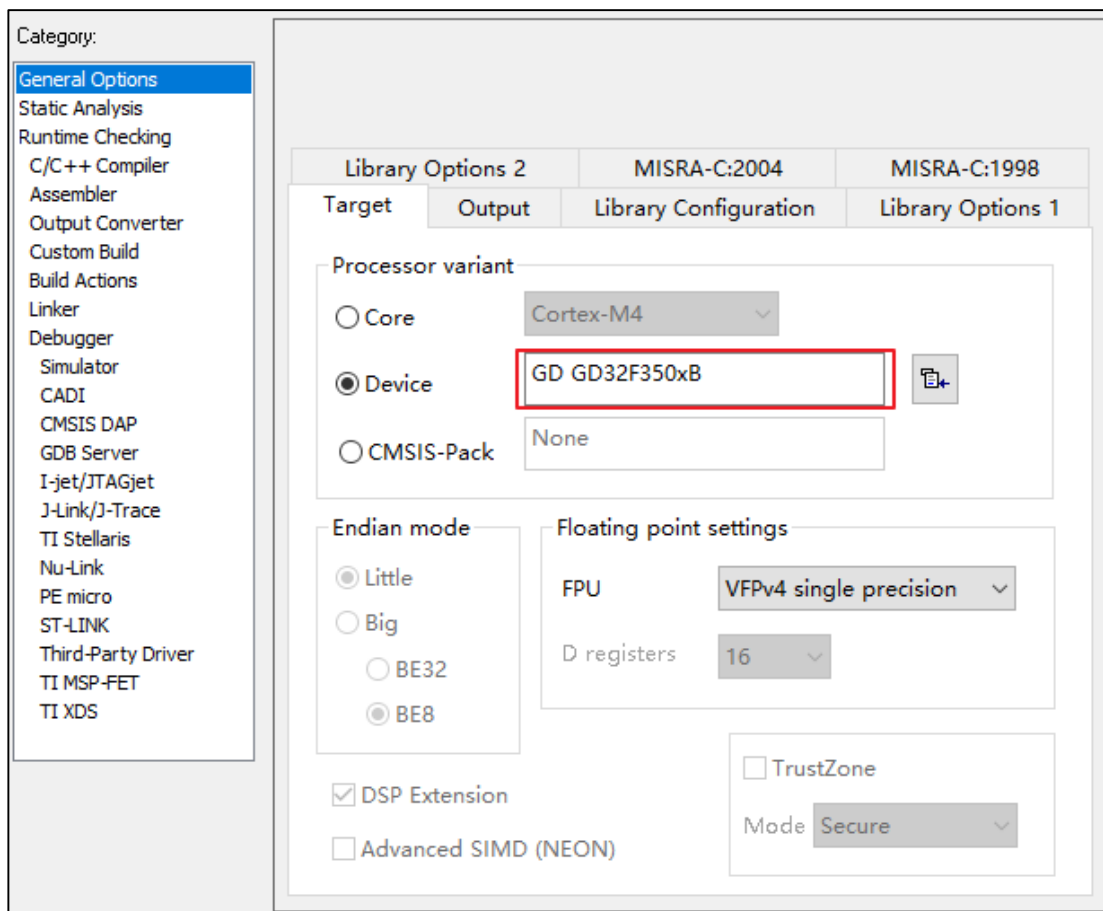
```

1  /*###ICF### Section handled by ICF editor, don't touch! ****/
2  /*-Editor annotation file-*/
3  /* IcfEditorFile="$TOOLKIT_DIR$\config\ide\IcfEditor\cortex_v1_0.xml" */
4  /*-Specials-*/
5  define symbol __ICFEDIT_intvec_start__ = 0x08000000;
6  /*-Symbols-*/
7  define symbol __ICFEDIT_region_ROM_start__ = 0x08000000;
8  define symbol __ICFEDIT_region_ROM_end__ = 0x0801FFFF;
9  define symbol __ICFEDIT_region_RAM_start__ = 0x200000B0;
10 define symbol __ICFEDIT_region_RAM_end__ = 0x20003FFF;
11 define symbol __ICFEDIT_region_IECTEST_PARAM_start__ = 0x20000040;
12 define symbol __ICFEDIT_region_IECTEST_PARAM_end__ = 0x200000B0;

```

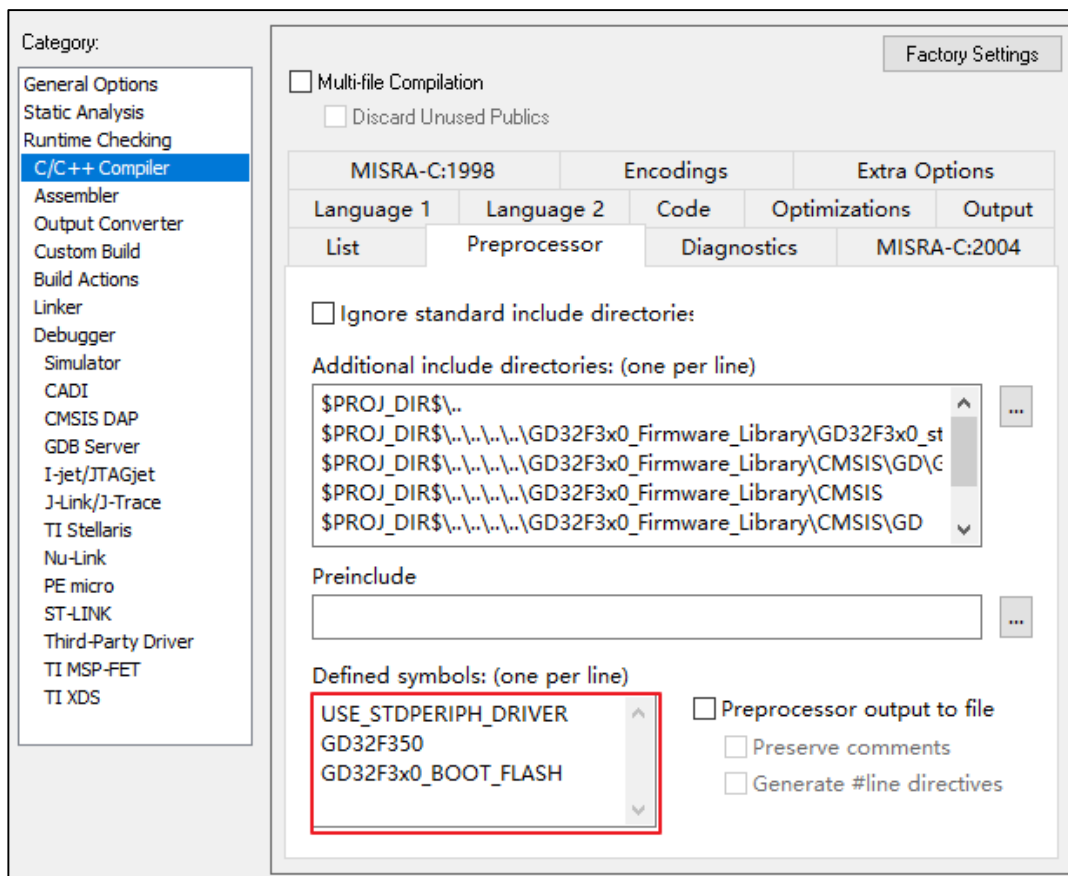
3、修改Options for node 'Project'中Target的配置，选择当前芯片的型号，如[图2-5. Device配置](#)所示：

图 2-5. Device 配置



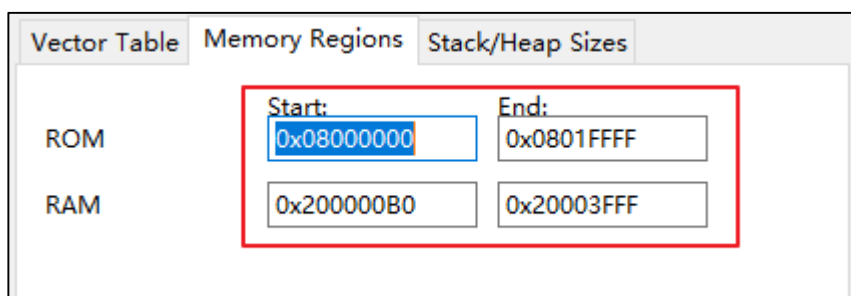
4、在Options for node 'Project'->C/C++ Compiler->Preprocessor中添加当前工程需要的预编译宏，主要修改符合当前芯片类型的预编译宏，如[图2-6. 修改预编译宏](#)所示：

图 2-6. 修改预编译宏



5、点击Options for node 'Project'->Linker->config->Edit->Memory Regions，根据当前芯片的数据手册修改ROM (Flash)和RAM的边界值，如 [图2-7. 修改工程设置中的边界值](#)所示。

图 2-7. 修改工程设置中的边界值



6、在Options for node 'Project'->Linker->Checksum中，修改End address为Flash大小，如 [图2-8. 修改工程属性中的Checksum配置](#)所示，在Extra Options选项卡中添加“--keep__checksum”。

图 2-8. 修改工程属性中的 Checksum 配置

Config	Library	Input	Optimizations	Advanced	Output	List
#define	Diagnostics	Checksum	Encodings	Extra Options		
<input checked="" type="checkbox"/> Fill unused code memory Fill pattern: <input type="text" value="0xFF"/> Start address: <input type="text" value="0x8000000"/> End address: <input type="text" value="0x801FFFF"/>						
<input checked="" type="checkbox"/> Generate checksum Checksum size: <input type="text" value="4 bytes"/> Alignment: <input type="text" value="4"/> Algorithm: <input type="text" value="CRC polynomial"/> <input type="text" value="0x4C11DB7"/> <input type="checkbox"/> Result in full size Complement: <input type="text" value="As is"/> Initial value: <input type="text" value="0xFFFFFFFF"/> Bit order: <input type="text" value="MSB first"/> <input type="checkbox"/> Use as input <input type="checkbox"/> Reverse byte order within word Checksum unit size: <input type="text" value="32-bit"/>						

图 2-9. 在 Extra Options 选项卡中添加配置

Config	Library	Input	Optimizations	Advanced	Output	List
#define	Diagnostics	Checksum	Encodings	Extra Options		
<input checked="" type="checkbox"/> Use command line options Command line options: (one per line)						
<pre>--keep _checksum</pre>						

2.2. Keil 环境认证库工程移植

1、根据当前芯片型号的数据手册修改gd32f3x0_test.h文件中RAM和Flash边界，如[图2-10. 修改gd32f3x0_test.h文件中RAM和Flash边界](#)所示。

图 2-10. 修改 gd32f3x0_test.h 文件中 RAM 和 Flash 边界

```

#if defined (__ARMCC_VERSION) && (__ARMCC_VERSION >= 6010050)

#define FLASH_START          ((uint32_t *)0x08000000)
#define FLASH_SIZE           ((uint32_t)0x00020000 - 4)
#define FLASH_SIZE_WORDS    ((uint32_t)((uint32_t)FLASH_END - (uint32_t)FLASH_START) / 4)
#define FLASH_END            ((uint32_t *)0x08020000)

#define FLASH_BLOCK_SIZE    ((uint32_t)512uL)
#define FLASH_BLOCKNUM      ((uint32_t)((uint32_t)FLASH_END - (uint32_t)FLASH_START) / FLASH_BLOCK_SIZE)
#define FLASH_BLOCKNUM_WORDS ((uint32_t)((FLASH_SIZE_WORDS) / FLASH_BLOCK_SIZE)

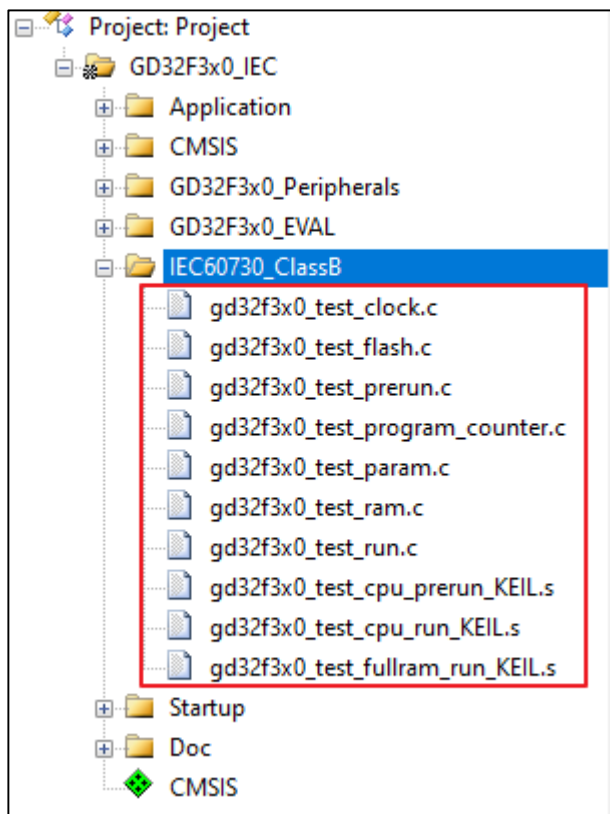
#define IEC_TEST_PARAM_START ((uint32_t *)0x20000040)
#define IEC_TEST_PARAM_END   ((uint32_t *)0x20000080)

#define RAM_START            (uint32_t *)0x20000000
#define RAM_END              (uint32_t *)0x20003F40

extern void Reset_Handler(void);
#define DefaultSystemStartUp() Reset_Handler()
void test_fail_reset(void);

#endif /* (__ARMCC_VERSION) && (__ARMCC_VERSION >= 6010050) */
    
```

图 2-11. 添加 ClassB 库文件到 Keil 工程



若启动文件适用当前芯片型号，则无需修改；否则需要在固件库文件夹 GD32F3x0_Firmware_Library\CMSIS\GD\GD32F3x0\Source\ARM下，重新选择适用当前芯片型号的.s启动文件，并做如下代码中红色标注所示修改：

Stack_Size	EQU	0x00000400
------------	-----	------------

```

                AREA    STACK, NOINIT, READWRITE, ALIGN=3
Stack_Mem      SPACE   Stack_Size
__initial_sp

; <h> Heap Configuration
;   <o>  Heap Size (in Bytes) <0x0-0xFFFFFFFF:8>
; </h>

Heap_Size     EQU     0x00000400

                AREA    HEAP, NOINIT, READWRITE, ALIGN=3
__heap_base
Heap_Mem      SPACE   Heap_Size
__heap_limit

                IMPORT  test_prerun

                PRESERVE8
                THUMB

;                /* reset Vector Mapped to at Address 0 */
                AREA    RESET, DATA, READONLY
                EXPORT  __Vectors
                EXPORT  __Vectors_End
                EXPORT  __Vectors_Size

__Vectors     DCD     __initial_sp          ; Top of Stack
                DCD     test_prerun         ; Reset Handler --> test_prerun
                DCD     NMI_Handler        ; NMI Handler
                .....
                .....
                .....
                DCD     USBFS_IRQHandler   ; 83:USBFS

__Vectors_End

                AREA CHECKSUM, DATA, READONLY, ALIGN=2
                EXPORT  __Check_Sum
                ALIGN
__Check_Sum   DCD 0xEEF15A05

```

```

__Vectors_Size EQU      __Vectors_End - __Vectors

                AREA    |.text|, CODE, READONLY

; /* reset Handler */
Reset_Handler  PROC
                .....
                .....
                .....

```

2、修改分散加载文件IEC_TEST_BOOT_FLASH.sct中的代码，如下表红色标注为需要修改的部分（根据当前芯片的数据手册修改Flash边界；修改与.s启动文件相对应.o文件的名称）：

```

; *****
; *****
; *** Scatter-Loading Description File generated by uVision ***
; *****

LR_IROM1 0x08000000 0x0001FFF8{
    ER_IROM1 0x08000000 0x0001FFF8{
        *.o (RESET, +First)
        *(InRoot$$Sections)
        .ANY (+RO)
    }

    .....

    .....

    .....

; RW data

RW_IRAM1 0x200000B0 0x00020000
{
    .ANY (+RW +ZI)
}

; stack overflow test

STACK_IRAM2 0x200020B0 UNINIT 0x00001F40
{
    gd32f3x0_test_param.o (STACK_OV_TEST, .bss.STACK_OV_TEST)
}

```

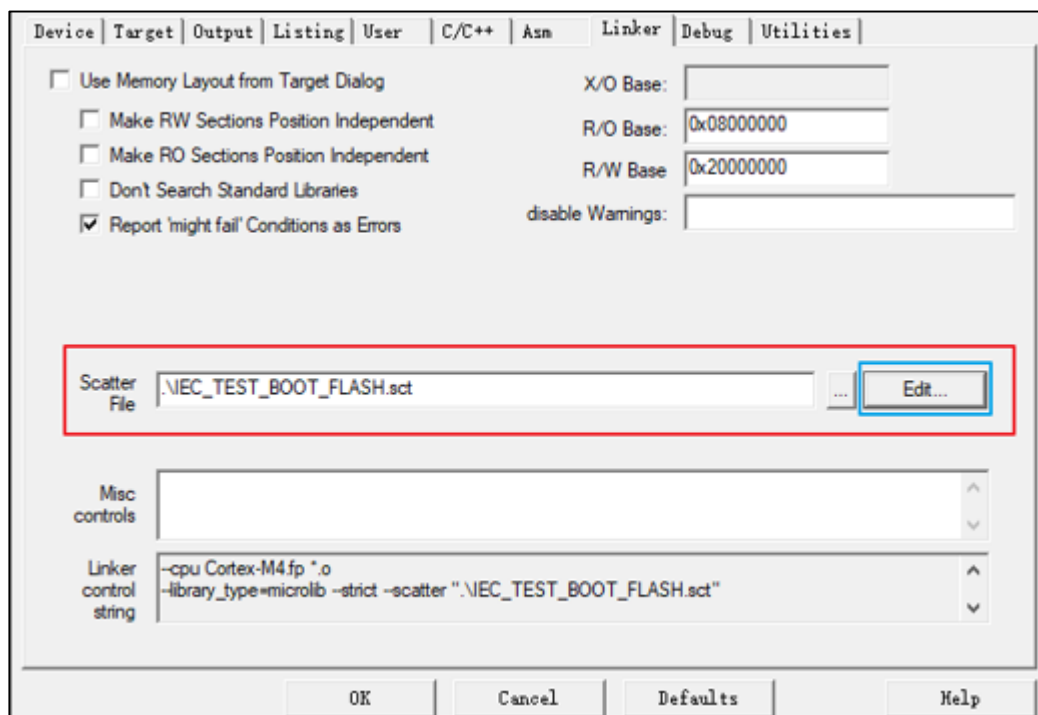
```

        startup_gd32f3x0.o (STACK, +Last)
    }
}

LR_IROM2 0x0801FFFC 0x0000004 {
    ER_IROM2 0x0801FFFC 0x0000004
    {
        *.o (CHECKSUM, +Last)
    }
}
    
```

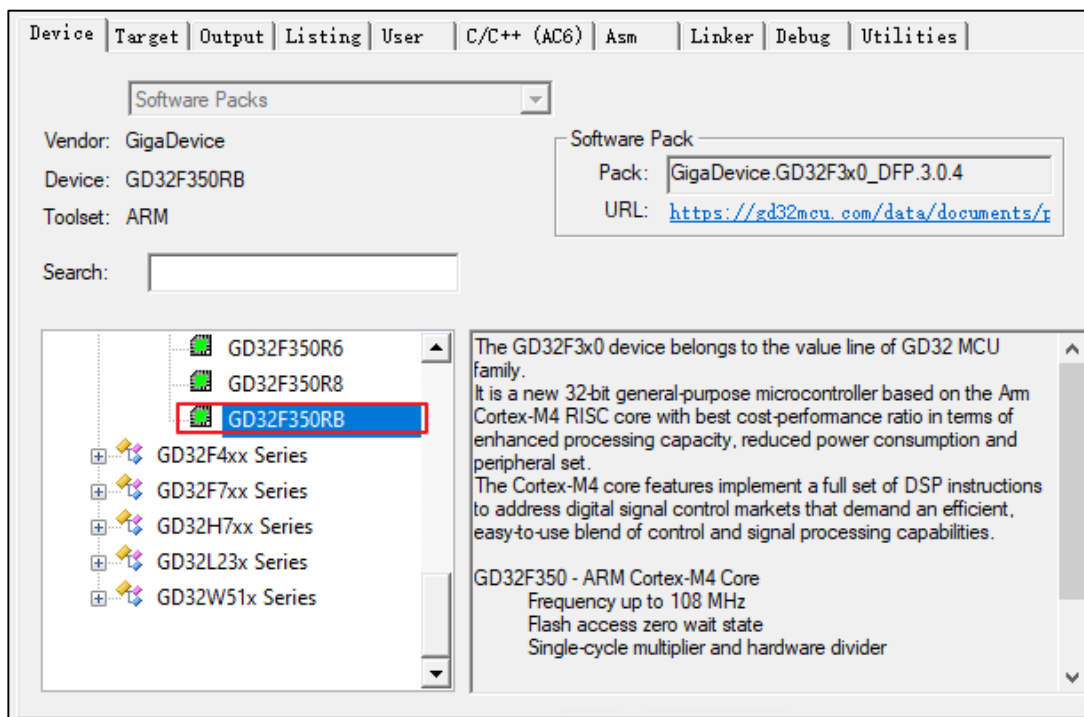
分散加载文件可在“Options for Target -->Linker-->Scatter File”中点击Edit按钮即可修改，如[图 2-12. 编辑分散加载文件](#)所示：

图 2-12. 编辑分散加载文件



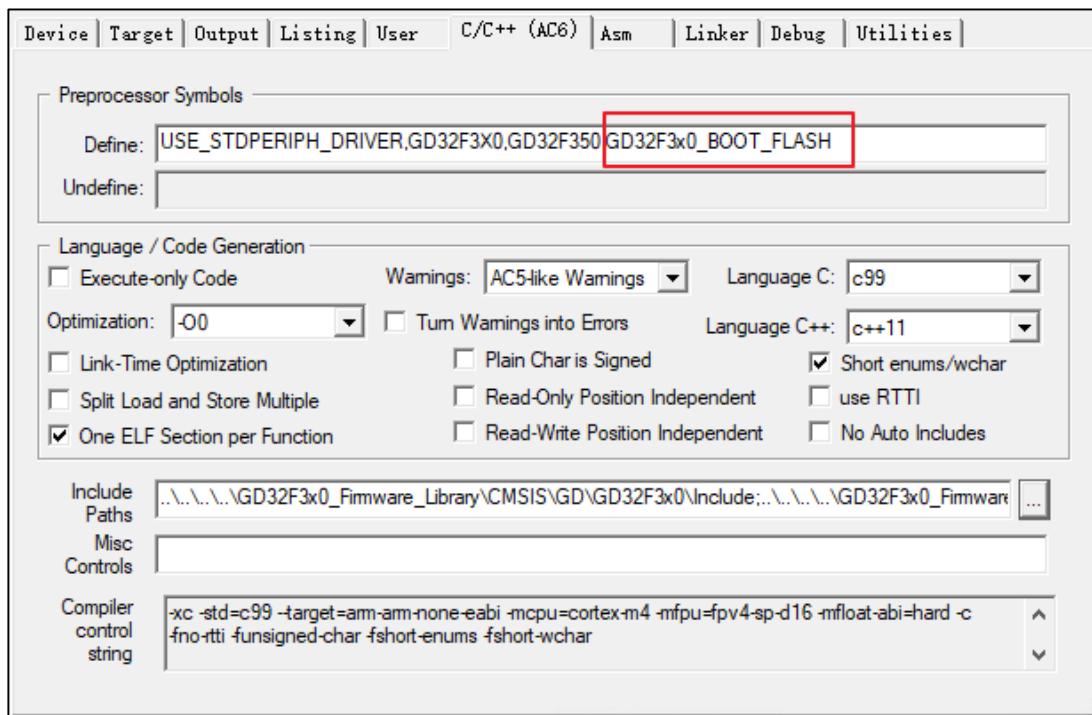
3、修改“Options for Target中DEVICE”的配置，选择当前芯片的型号，如[图2-13. Device配置](#)所示：

图 2-13. Device 配置



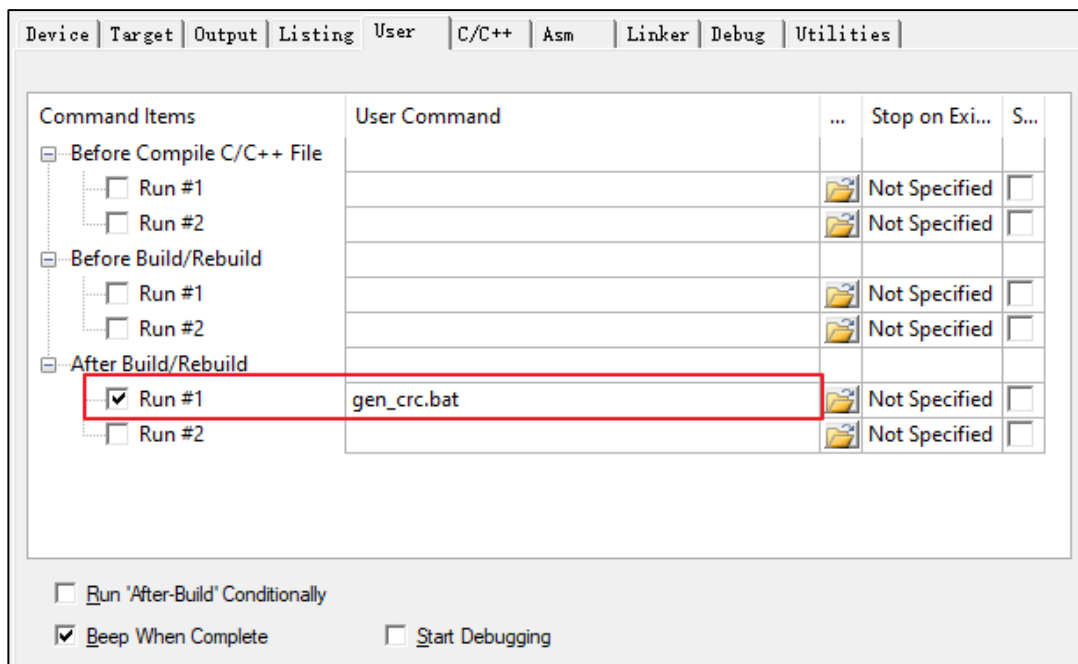
4、在Options for Target->C/C++->Preprocessor Symbols中添加当前工程需要的预编译宏与当前芯片一致，如 [图2-14. 修改预编译宏](#)所示：

图 2-14. 修改预编译宏



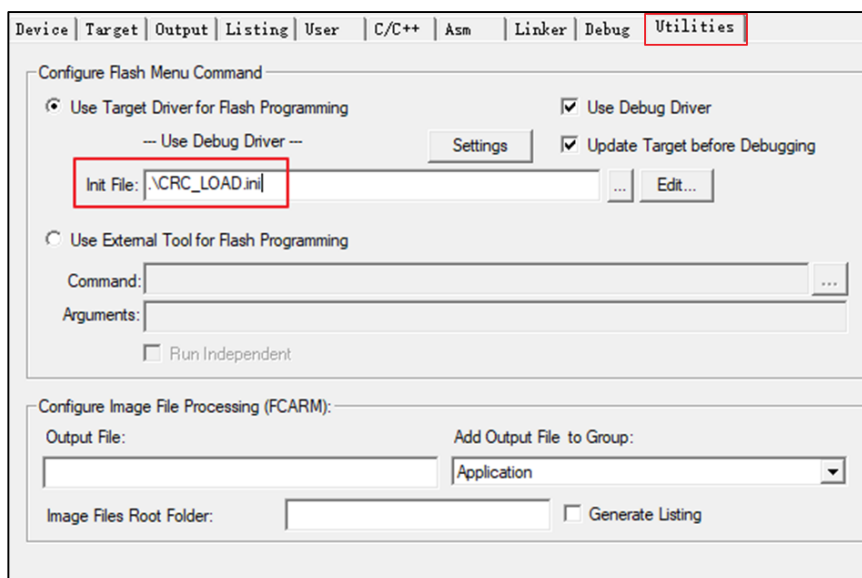
5、当需要使用批处理自动计算CRC时，需要添加gen_crc.bat文件，具体如 [图2-15. 添加批处理文件](#)。

图 2-15. 添加批处理文件



6、最后，在Utilities选项卡中选择CRC_LOAD.ini，具体如[图2-16. 添加.ini配置文件](#)所示。

图 2-16. 添加.ini 配置文件



2.3. eclipse 环境认证库工程移植

认证库工程在各个环境下的移植步骤类似，但是各开发环境下的编译链有所区别，导致 RAM 和 Flash 边界设置有所不同，eclipse 环境下的移植步骤如下：

1、根据芯片数据手册修改gd32f3x0_test.h文件中编译宏__GNU__下的RAM边界，保证芯片的Flash和RAM全部空间得到检测，如[图2-17. 修改gd32f3x0_test.h中RAM边界](#)所示。

图 2-17. 修改 gd32f3x0_test.h 中 RAM 边界

```

#ifndef (__ARMCC_VERSION) && (__GNUC__)
#define FLASH_START          ((uint32_t *)0x08000000)
#define FLASH_SIZE           ((uint32_t)FLASH_END-(uint32_t)FLASH_START)
#define FLASH_SIZE_WORDS    ((uint32_t)((uint32_t)FLASH_END-(uint32_t)FLASH_START)/4)
#define FLASH_END           ((uint32_t *)0x0801FFC0)

#define FLASH_BLOCK_SIZE    ((uint32_t)512uL)
#define FLASH_BLOCKNUM     ((uint32_t)((uint32_t)FLASH_END-(uint32_t)FLASH_START) / FLASH_BLOCK_SIZE)
#define FLASH_BLOCKNUM_WORDS ((uint32_t)((FLASH_SIZE_WORDS) / FLASH_BLOCK_SIZE)

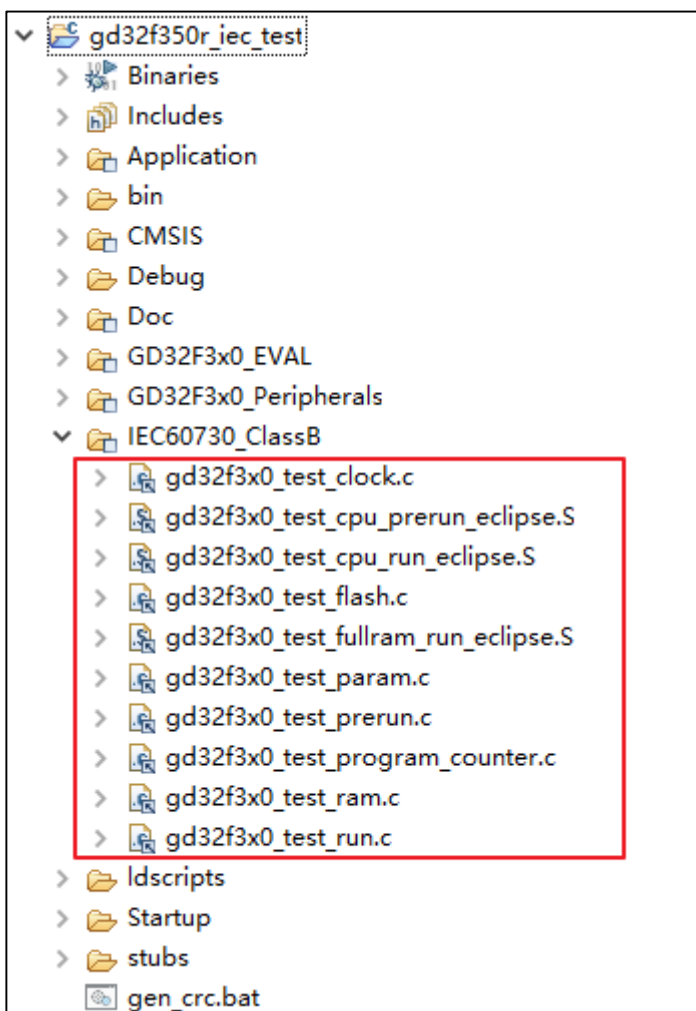
#define IEC_TEST_PARAM_START ((uint32_t *)0x20000040)
#define IEC_TEST_PARAM_END  ((uint32_t *)0x200000B0)

#define RAM_START           ((uint32_t *)0x20000000)
#define RAM_DATAAREA_END   ((uint32_t *) (0x200000B0 - 0x40))
#define RAM_STACK_START    ((uint32_t *)0x20003800)
#define RAM_END             ((uint32_t *)0x20003FC0)

#define DefaultSystemStartUp()
void test_fail_reset(void);

#endif /* (__ARMCC_VERSION) && (__GNUC__) */
    
```

图 2-18. 添加 ClassB 库文件到 eclipse 工程



若启动文件适用当前芯片型号，则无需修改；若不符合，则需重新选择符合当前芯片类型的.s 启动文件，并如 [图2-19. 修改启动文件](#)所示进行修改，使芯片在运行之前进行自检。

图 2-19. 修改启动文件

```
48
49 bl test_prerun /* SystemInit */
50
51 /* Call SystemInit function */
52 bl SystemInit
53 /* Call static constructors */
54 // bl __libc_init_array
55 /* Call the main function */
56 bl main
57 bx lr
58 .size Reset_Handler, .-Reset_Handler
59
60
61
62 .section .text.Default_Handler,"ax",%progbits
63 Default_Handler:
64 Infinite_Loop:
65 b Infinite_Loop
66 .size Default_Handler, .-Default_Handler
67
68
69 .section .isr_vector,"a",%progbits
70 .global __gVectors
71
72
73
74 __gVectors:
75 .word _estack /* Top of Stack */
```

2、修改如[图2-20. 分散加载文件位置](#)目录下的分散加载文件，如[图2-21. 修改eclipse工程分散加载文件](#)所示为修改的部分，根据芯片数据手册修改Flash和RAM的大小适配当前芯片。

图 2-20. 分散加载文件位置

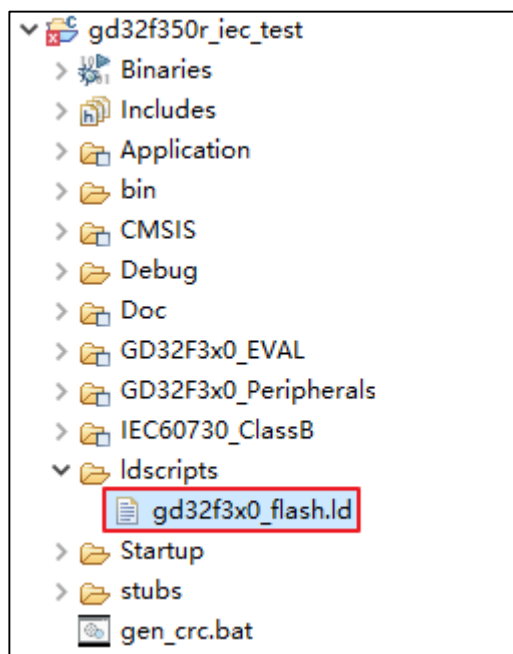


图 2-21. 修改 eclipse 工程分散加载文件

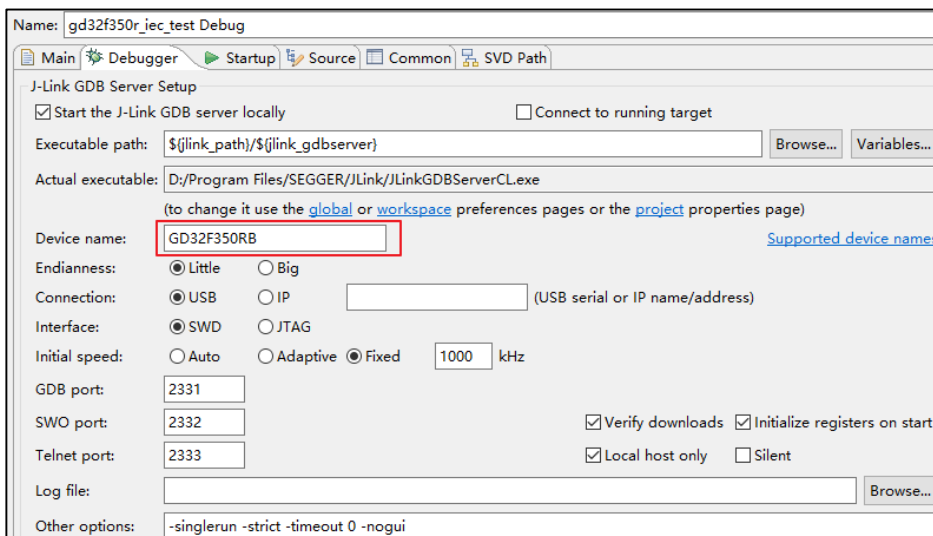
```

1
2 ENTRY(Reset_Handler)
3
4 /* end of Stack */
5 _estack = 0x20004000;
6
7 /* memory map */
8 MEMORY
9 {
10 FLASH (rx) : ORIGIN = 0x08000000, LENGTH = 128K
11 iec_test (wxa!ri) : ORIGIN = 0x20000000, LENGTH = 0xB0
12 RAM (xrw) : ORIGIN = 0x200000B0, LENGTH = 0x3F50 /*8K*/
13 flash_end (rxai!w) : ORIGIN = 0x0801FFC0 LENGTH = 0x40
14 }

```

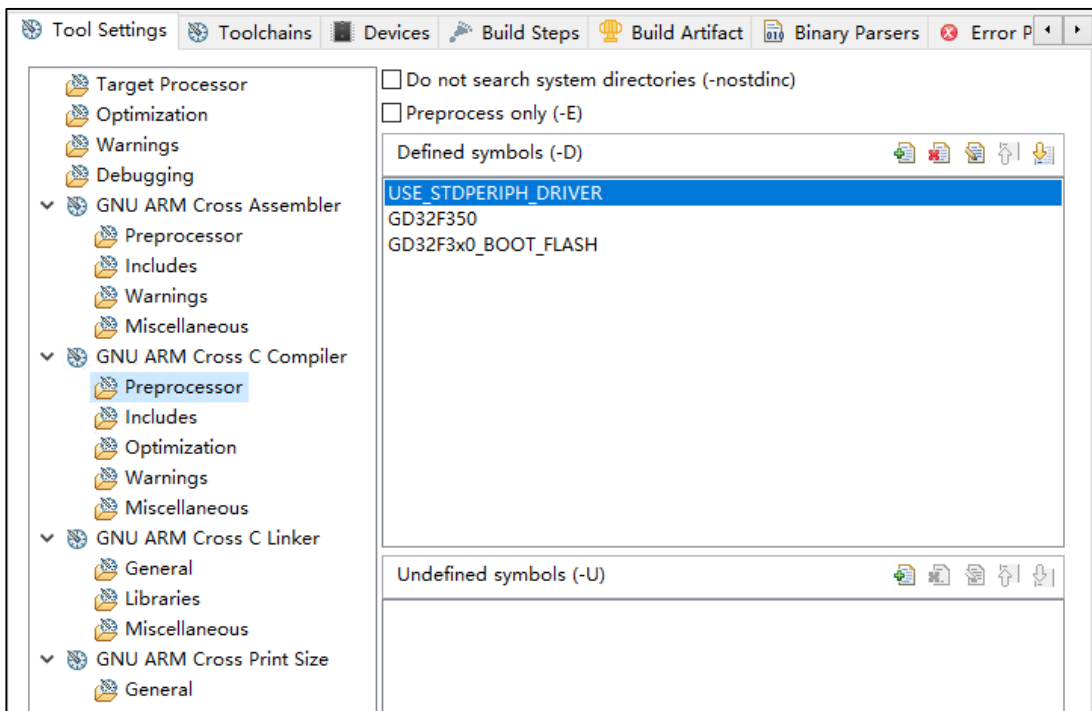
3、修改“Debug Configurations->Debugger”中Device name的配置，选择当前芯片的型号，如 [图2-22. Device name配置](#)所示：

图 2-22. Device name 配置



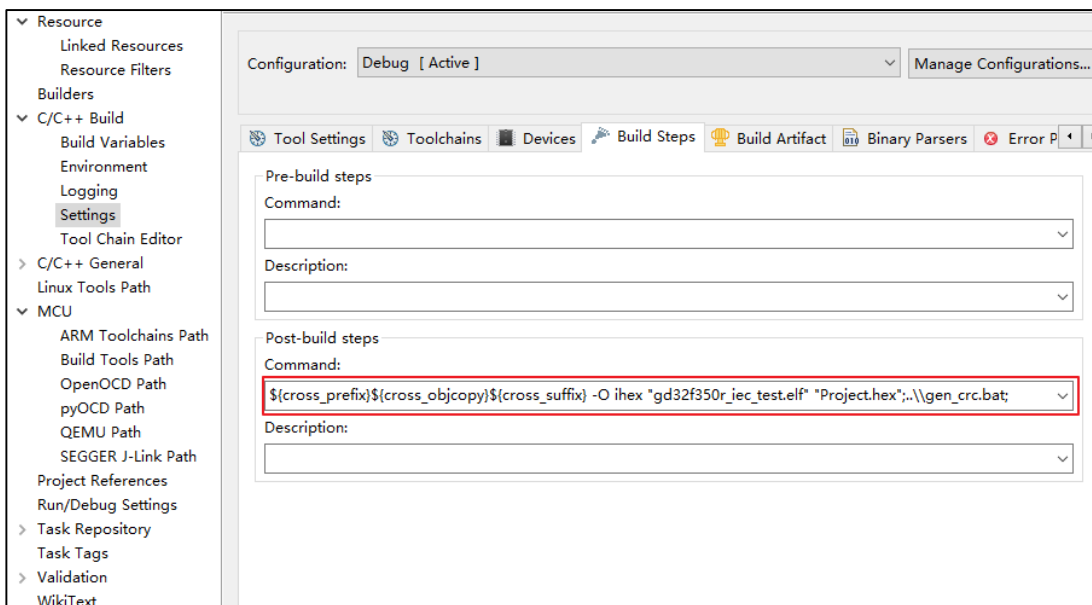
4、在工程属性“C/C++ Build->Settings->Tool Settings->Cross ARM GNU Assembler->Preprocessor”和“C/C++ Build->Settings->Tool Settings->Cross ARM GNU C Compiler->Preprocessor”中添加当前工程需要的预编译宏，主要修改符合当前芯片类型的预编译宏（如 [图2-23. 修改汇编编译器预编译宏](#)所示。

图 2-23. 修改汇编编译器预编译宏



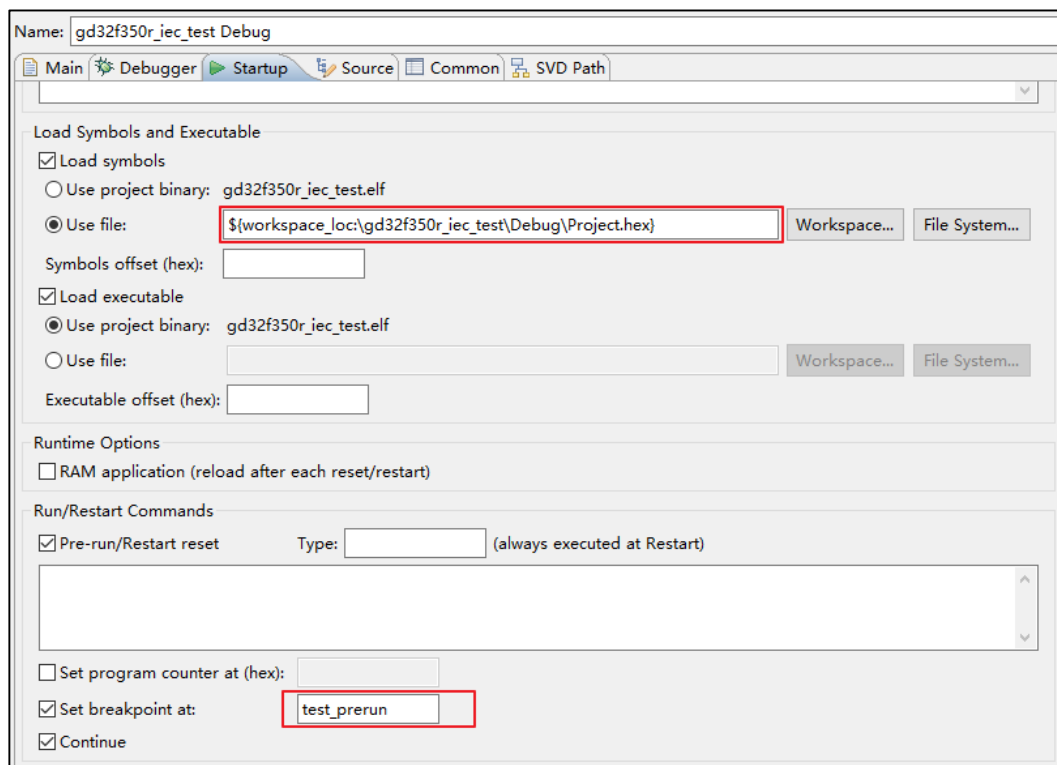
5、修改“C++ Build->Settings->Build Steps->Post-build steps->Command”中的命令，如 [图2-24](#) [修改Post-build指令](#)所示更换为当前工程名称的elf文件。

图 2-24. 修改 Post-build 指令



6、修改“Debug Configurations->Startup”中的可执行文件的配置，选择当前工作空间中编译生成的Project.hex文件，如 [图2-25](#) [修改可执行文件配置](#)所示：

图 2-25. 修改可执行文件配置



4. 版本历史

表 4-1. 版本历史

版本号	说明	日期
1.0	首次发布	2023 年 08 月 01 日

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